

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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1200 V  $V_{CES}$ 

38A

V<sub>CE(sat)</sub> = 1.8V

# Single IGBT

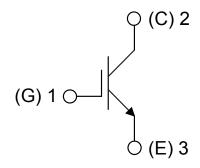
**XPT IGBT** 

#### Part number

#### IXA20I1200PB



Backside: collector



#### Features / Advantages:

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
- short circuit rated for 10 µsec.
- very low gate charge
- low EMI
- square RBSOA @ 3x Ic
- Thin wafer technology combined with the XPT design results in a competitive low VCE(sat)

#### Applications:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipmentSwitched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

#### Package: TO-220

- · Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0





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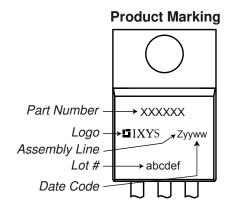
IGBT					1	Ratings	;	
Symbol	Definition		Conditions		min.	typ.	max.	Unit
V <sub>CES</sub>	collector emitter voltage			$T_{VJ} = 25^{\circ}C$			1200	V
V <sub>GES</sub>	max. DC gate voltage						±20	V
$V_{\text{GEM}}$	max. transient gate emitter voltage						±30	V
I <sub>C25</sub>	collector current			$T_C = 25^{\circ}C$			38	Α
I <sub>C80</sub>				$T_{c} = 80^{\circ}C$			22	Α
P <sub>tot</sub>	total power dissipation			$T_{C} = 25^{\circ}C$			165	W
V <sub>CE(sat)</sub>	collector emitter saturation voltage		I <sub>C</sub> = 15A; V <sub>GE</sub> = 15 V	$T_{VJ} = 25^{\circ}C$		1.8	2.1	V
				$T_{VJ} = 125^{\circ}C$		2.1		V
$V_{GE(th)}$	gate emitter threshold voltage		$I_C$ = 0.6mA; $V_{GE}$ = $V_{CE}$	$T_{VJ} = 25^{\circ}C$	5.4	5.9	6.5	V
I <sub>CES</sub>	collector emitter leakage current		$V_{CE} = V_{CES}$ ; $V_{GE} = 0 \text{ V}$	$T_{VJ} = 25^{\circ}C$			0.1	mA
				$T_{VJ} = 125^{\circ}C$		0.1		mΑ
I <sub>GES</sub>	gate emitter leakage current		$V_{GE} = \pm 20 \text{ V}$				500	nA
Q <sub>G(on)</sub>	total gate charge		$V_{CE}$ = 600 V; $V_{GE}$ = 15 V; $I_{C}$ =	15 A		47		nC
t <sub>d(on)</sub>	turn-on delay time	$\overline{}$				70		ns
t <sub>r</sub>	current rise time		industive lead	T - 405°C		40		ns
$t_{d(off)}$	turn-off delay time		inductive load	$T_{VJ} = 125^{\circ}C$		250		ns
$t_f$	current fall time		$V_{CE} = 600 \text{ V}; I_C = 15 \text{ A}$			100		ns
E <sub>on</sub>	turn-on energy per pulse		$V_{GE} = \pm 15 \text{ V}; R_G = 56 \Omega$			1.65		mJ
$E_{off}$	turn-off energy per pulse	J				1.7		mJ
RBSOA	reverse bias safe operating area	٦	$V_{GE} = \pm 15 \text{ V}; R_{G} = 56 \Omega$	T <sub>VJ</sub> = 125°C				
I <sub>CM</sub>			$V_{CEmax} = 1200 V$				45	Α
SCSOA	short circuit safe operating area	$\overline{}$	V <sub>CEmax</sub> = 900 V					
tsc	short circuit duration	>	$V_{CE} = 900 V; V_{GE} = \pm 15 V$	$T_{VJ} = 125^{\circ}C$			10	μs
I <sub>sc</sub>	short circuit current	J	$R_G$ = 56 $\Omega$ ; non-repetitive			60		Α
R <sub>thJC</sub>	thermal resistance junction to case						0.76	K/W
R <sub>thCH</sub>	thermal resistance case to heatsink					0.50		K/W



## IXA20I1200PB

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Package TO-220				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I <sub>RMS</sub>	RMS current	per terminal			35	Α	
T <sub>VJ</sub>	virtual junction temperature		-40		150	°C	
T <sub>op</sub>	operation temperature		-40		125	°C	
T <sub>stg</sub>	storage temperature		-40		150	°C	
Weight				2		g	
M <sub>D</sub>	mounting torque		0.4		0.6	Nm	
F <sub>c</sub>	mounting force with clip		20		60	Ν	



#### Part number

I = IGBT

X = XPT IGBT

A = Gen 1 / std 20 = Current Rating [A]

I = Single IGBT

1200 = Reverse Voltage [V] PB = TO-220AB (3)

(	Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
5	Standard	IXA20I1200PB	IXA20I1200PB	Tube	50	507929

Similar Part	Package	Voltage class
IXA20IF1200HB	TO-247AD (3)	1200

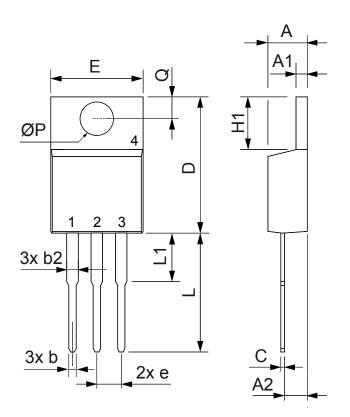
Equiva	alent Circuits for Simulation	* on die level	T <sub>VJ</sub> = 150 °C
$I \rightarrow V_0$	$R_0$	IGBT	
V <sub>0 max</sub>	threshold voltage	1.1	V
R <sub>0 max</sub>	slope resistance *	86	$m\Omega$





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### Outlines TO-220



Dim.	Millimeter		Inches		
	Min.	Max.	Min.	Max.	
Α	4.32	4.82	0.170	0.190	
A1	1.14	1.39	0.045	0.055	
A2	2.29	2.79	0.090	0.110	
b	0.64	1.01	0.025	0.040	
b2	1.15	1.65	0.045	0.065	
С	0.35	0.56	0.014	0.022	
D	14.73	16.00	0.580	0.630	
Е	9.91	10.66	0.390	0.420	
е	2.54	BSC	0.100	BSC	
H1	5.85	6.85	0.230	0.270	
L	12.70	13.97	0.500	0.550	
L1	2.79	5.84	0.110	0.230	
ØP	3.54	4.08	0.139	0.161	
Q	2.54	3.18	0.100	0.125	

